# DOCUMENT CHANGE REQUEST

DCR number 1582

Changes required for: General

Originator: Steve Thacker

Date: 2023/09/12

Date sent: 2023/06/28

Organisation: ESCC Executive Secretariat

Status: IMPLEMENTED

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|---|---|---|---|
| Title: | TRANSISTORS, POWER, MOSFET, N CHANNEL, RAD-HARD BASED ON TYPES BUY06CS35J-01, | | |
| Number: | 5205/032 | Issue: | 2 |

Other documents affected:

Page:

Various; see attached

Paragraph:

Various; see attached & below

Original wording:

As per 5205/032 issue 2

Proposed wording:

Amend, for Variant 06 only, the maximum Static Drain-to-Source On Resistance, rDS(on), throughout this specification; to be as follows (see attached for details, with changes highlighted yellow):
a) In Para. 1.4.2, 2.5.1, 2.6, 2.7, 2.11.2:
Variant 06: change maximum limit for rDS(on) to be 7mohm (was 6.5mohm)

b) In Para. 2.5.2:
Variant 06: change maximum limit for rDS(on) to be 10.5mohm (was 10mohm)

Justification:

This DCR is raised on behalf of Manufacturer Infineon.

Infineon stated that, as previously discussed with ESA/Tesat/DLR, this marginal increase in maximum rDS(on) is required for the new (in 2023) Variant 06 due to:
"a shift of the RDSon distribution towards higher values (for new Variant 06 only). However we (Infineon) do not see any impact on the reliability of the device".

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| Attachments: |
| escc5205032iss_draft_3a_for_review.docx |
| Modifications: |
| N/A |
| Approval signature: |
| |
| Date signed: |
| 2023-09-12 |